

Silicon NPN Power Transistors

2SC2934

DESCRIPTION

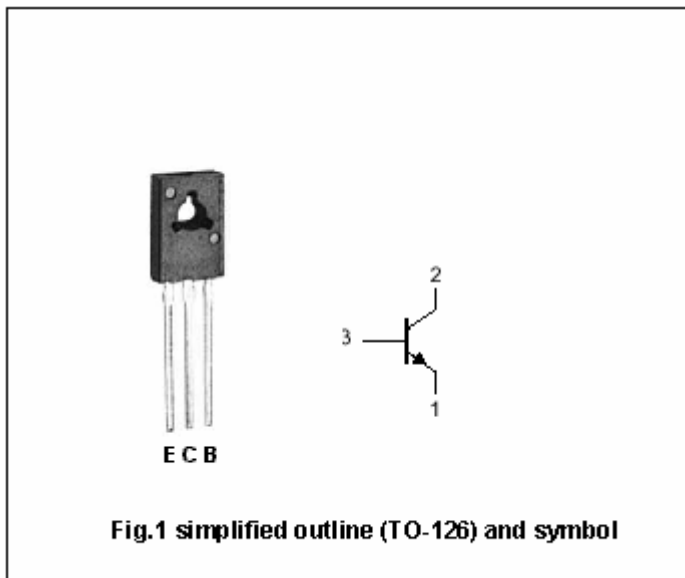
- With TO-126 package
- High  $V_{CEO}$
- Low  $C_{OB}$

APPLICATIONS

- For TV video output amplification

PINNING □ see Fig.2 □

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	300	V
$V_{CEO}$	Collector-emitter voltage	Open base	300	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		0.2	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	12.5	W
$T_j$	Junction temperature		150	□
$T_{stg}$	Storage temperature		-55~150	□

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =5mA			1.5	V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =10μA; I <sub>E</sub> =0	300			V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =100μA; I <sub>B</sub> =0	300			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10μA; I <sub>C</sub> =0	7			V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =200V; I <sub>E</sub> =0			0.1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =50mA ; V <sub>CE</sub> =10V	50		300	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =20mA ; V <sub>CE</sub> =20V		80		MHz

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PACKAGE OUTLINE

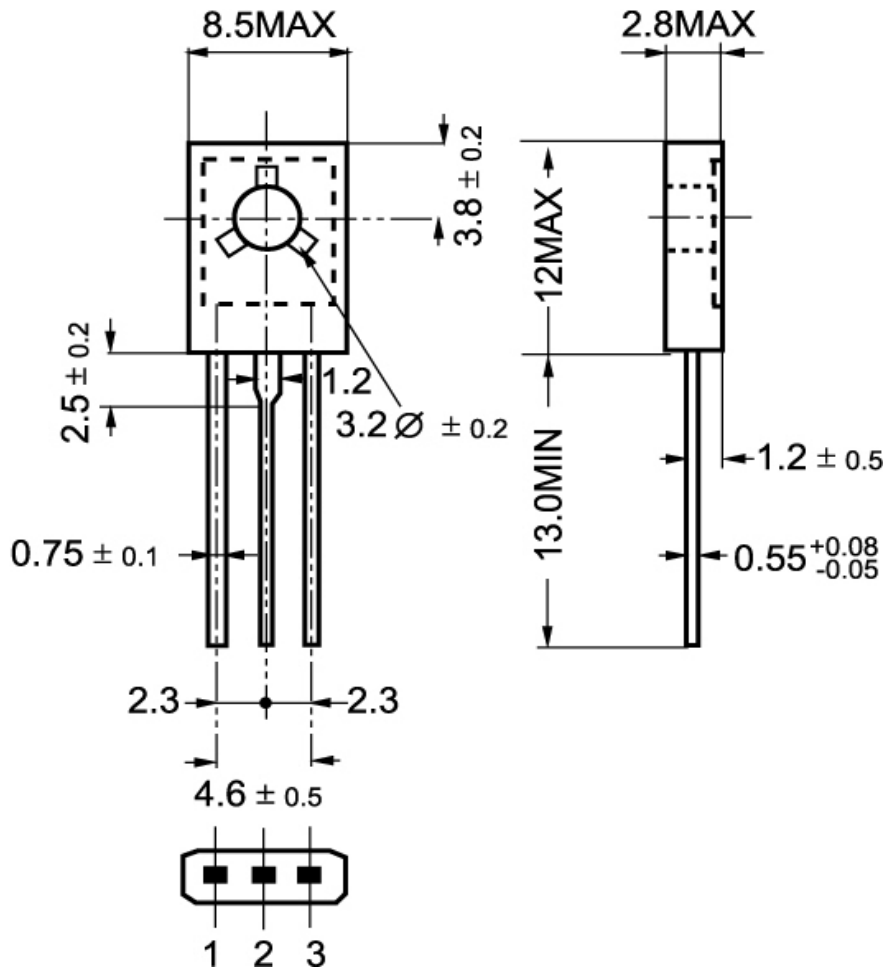


Fig.2 outline dimensions